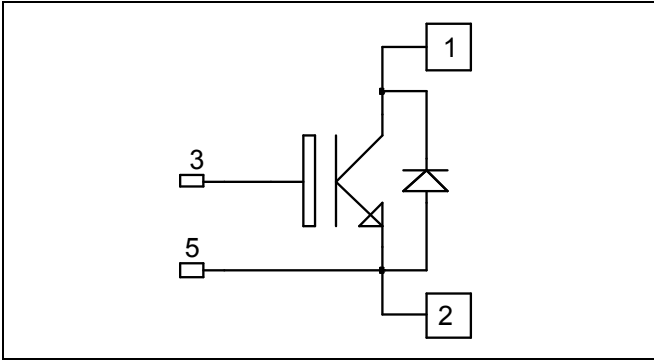


Single switch
NPT IGBT Power Module

$V_{CES} = 600V$
 $I_C = 660A @ T_c = 80^{\circ}C$

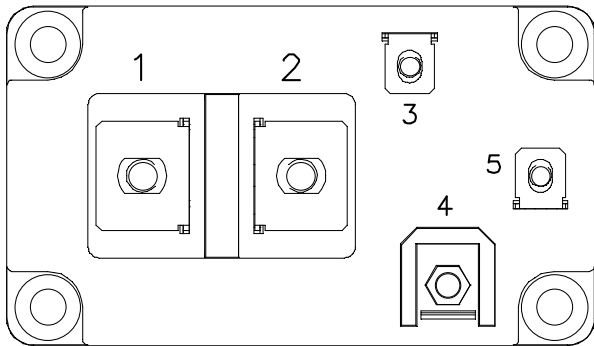


Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Non Punch Through (NPT) IGBT
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 50 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- M6 connectors for power
- M4 connectors for signal
- High level of integration



Benefits

- Outstanding performance at high frequency operation
- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive T_C of V_{CEsat}
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage	600	V
I_C	Continuous Collector Current	$T_C = 25^{\circ}C$	860
		$T_C = 80^{\circ}C$	660
I_{CM}	Pulsed Collector Current	$T_C = 25^{\circ}C$	1320
V_{GE}	Gate - Emitter Voltage	± 20	V
P_D	Maximum Power Dissipation	$T_C = 25^{\circ}C$	2800
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125^{\circ}C$	1600A@520V

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit	
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0\text{V}$ $V_{CE} = 600\text{V}$	$T_j = 25^\circ\text{C}$			500	μA
			$T_j = 125^\circ\text{C}$			1	mA
$V_{CE(sat)}$	Collector Emitter saturation Voltage	$V_{GE} = 15\text{V}$ $I_C = 800\text{A}$	$T_j = 25^\circ\text{C}$	1.95	2.45	V	
			$T_j = 125^\circ\text{C}$	2.2			
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 16\text{mA}$	4.5	5.5	6.5	V	
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20\text{V}, V_{CE} = 0\text{V}$			2400	nA	

Dynamic Characteristics

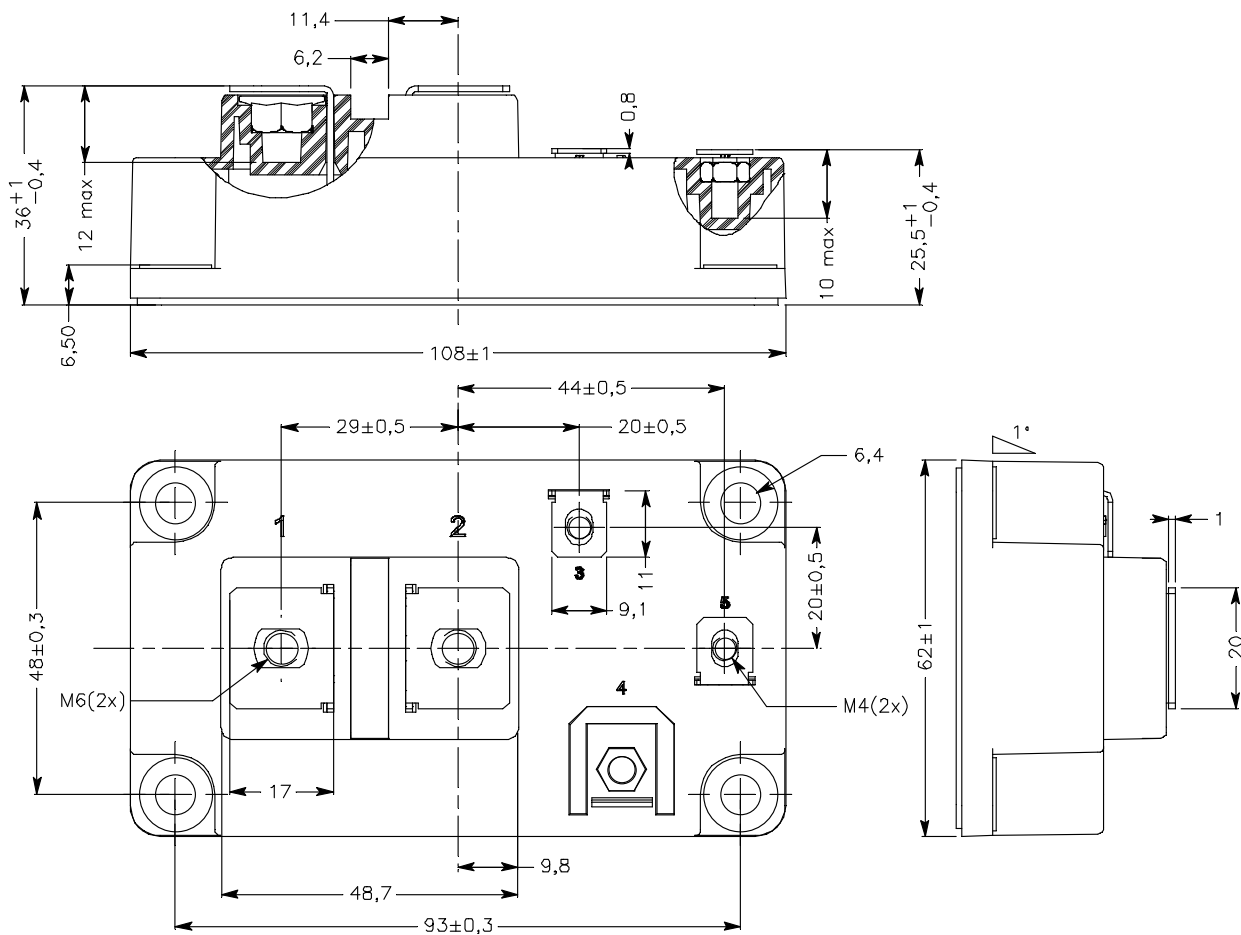
Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{ies}	Input Capacitance	$V_{GE} = 0\text{V}, V_{CE} = 25\text{V}$ $f = 1\text{MHz}$		36		nF
C_{res}	Reverse Transfer Capacitance			3.2		
Q_G	Gate charge	$V_{GE} = 15\text{V}, I_C = 800\text{A}$ $V_{CE} = 300\text{V}$		2		μC
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) $V_{GE} = \pm 15\text{V}$ $V_{Bus} = 300\text{V}$ $I_C = 800\text{A}$ $R_G = 16\Omega$		150		ns
T_r	Rise Time			72		
$T_{d(off)}$	Turn-off Delay Time			530		
T_f	Fall Time			40		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C) $V_{GE} = \pm 15\text{V}$ $V_{Bus} = 300\text{V}$ $I_C = 800\text{A}$ $R_G = 16\Omega$		160		ns
T_r	Rise Time			75		
$T_{d(off)}$	Turn-off Delay Time			550		
T_f	Fall Time			50		
E_{on}	Turn on Energy	$V_{GE} = \pm 15\text{V}$ $V_{Bus} = 300\text{V}$ $I_C = 800\text{A}$ $R_G = 16\Omega$	$T_j = 125^\circ\text{C}$	36		mJ
E_{off}	Turn off Energy		$T_j = 125^\circ\text{C}$	33		mJ
I_{sc}	Short Circuit data	$V_{GE} \leq 15\text{V}; V_{Bus} = 360\text{V}$ $t_p \leq 10\mu\text{s}; T_j = 125^\circ\text{C}$		3600		A

Reverse diode ratings and characteristics

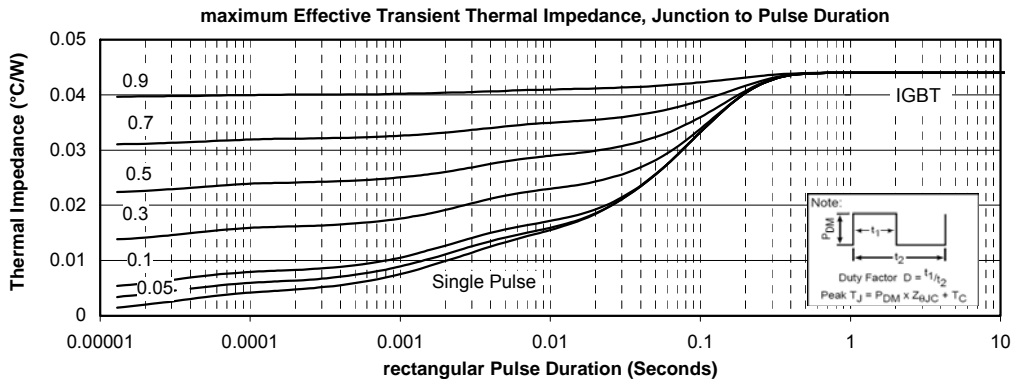
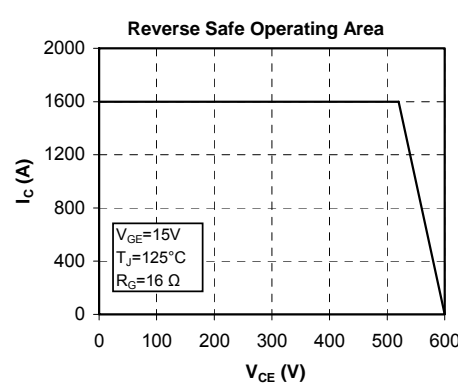
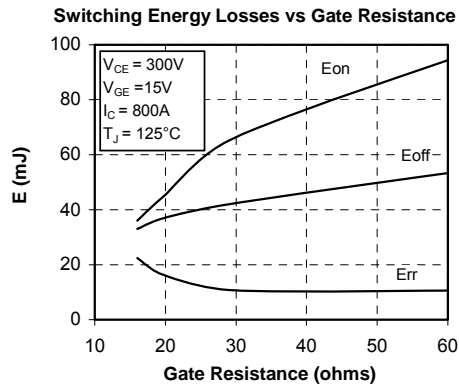
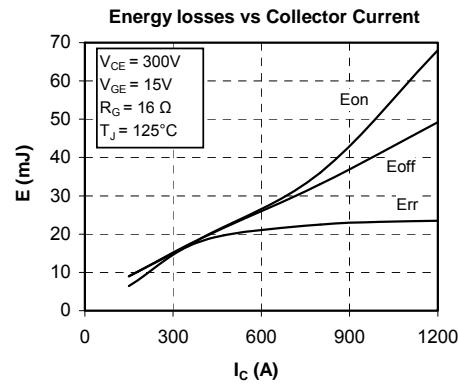
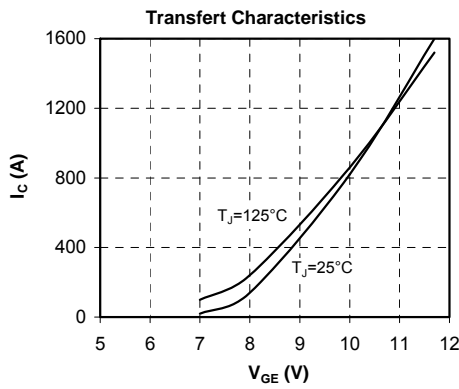
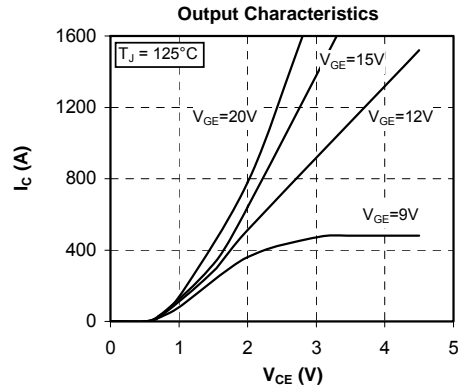
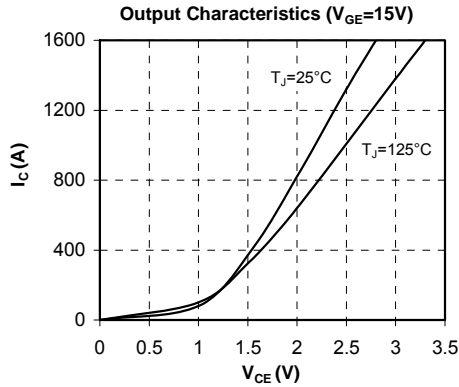
Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage		600			V
I_{RRM}	Maximum Reverse Leakage Current	$V_R = 600\text{V}$	$T_j = 25^\circ\text{C}$		750	μA
			$T_j = 125^\circ\text{C}$		1000	
I_F	DC Forward Current			800		A
V_F	Diode Forward Voltage	$I_F = 800\text{A}$ $V_{GE} = 0\text{V}$	$T_j = 25^\circ\text{C}$	1.25	1.6	V
			$T_j = 125^\circ\text{C}$	1.2		
t_{rr}	Reverse Recovery Time	$I_F = 800\text{A}$ $V_R = 300\text{V}$ $di/dt = 7000\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$	150		ns
			$T_j = 125^\circ\text{C}$	250		
Q_{rr}	Reverse Recovery Charge		$T_j = 25^\circ\text{C}$	57		μC
			$T_j = 125^\circ\text{C}$	80		
E_{rr}	Reverse Recovery Energy	$T_j = 25^\circ\text{C}$	11.6		mJ	
		$T_j = 125^\circ\text{C}$	22.8			

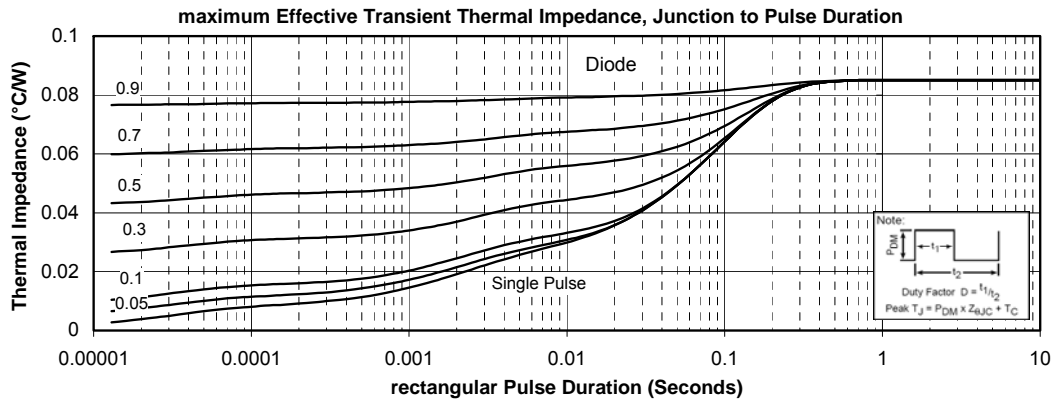
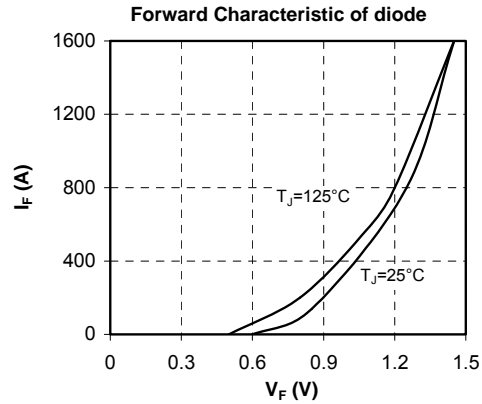
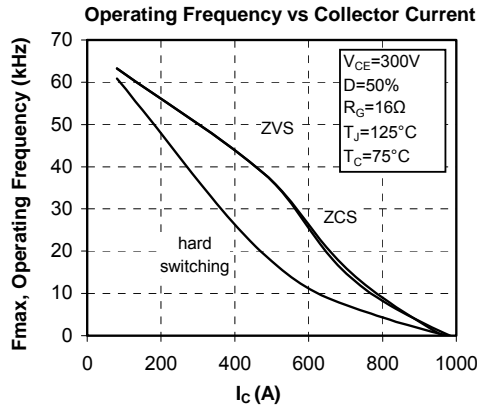
Thermal and package characteristics

Symbol	Characteristic	Min	Typ	Max	Unit
R _{thJC}	Junction to Case Thermal Resistance	IGBT		0.044	°C/W
		Diode		0.085	
V _{ISOL}	RMS Isolation Voltage, any terminal to case t = 1 min, I _{isol} < 1mA, 50/60Hz	2500			V
T _J	Operating junction temperature range	-40		150	°C
T _{STG}	Storage Temperature Range	-40		125	
T _C	Operating Case Temperature	-40		125	
Torque	Mounting torque	M6	3	5	N.m
		M4	1	2	
Wt	Package Weight			350	g

D4 Package outline (dimensions in mm)


Typical Performance Curve





Microsemi reserves the right to change, without notice, the specifications and information contained herein

Microsemi's products are covered by one or more of U.S. patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 6,939,743 7,352,045 5,283,201 5,801,417 5,648,283 7,196,634 6,664,594 7,157,886 6,939,743 7,342,262 and foreign patents. U.S. and Foreign patents pending. All Rights Reserved.